Dynamical polarization of graphene at nite doping

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A bstract

The polarization of graphene is calculated exactly within the random phase approximation for arbitrary frequency, wave vector, and doping. At nite doping, the static susceptibility saturates to a constant value for low momenta. At $q=2k_F$ it has a discontinuity only in the second derivative. In the presence of a charged impurity this results in Friedel oscillations which decay with the same power law as the Thomas Fermi contribution, the latter being always dominant. The spin density oscillations in the presence of a magnetic impurity are also calculated. The dynamical polarization for low q and arbitrary! is employed to calculate the dispersion relation and the decay rate of plasmons and acoustic phonons as a function of doping. The low screening of graphene, combined with the absence of a gap, leads to a signicant stiening of the longitudinal acoustic lattice vibrations.

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I. INTRODUCTION

Recent progress in the isolation of single graphene layers has perm itted the realization of transport and Ram an experim ents¹ which have stimulated an intense theoretical research on the properties of a monoatom ic graphene sheet. Most of the unusual electronic properties can be understood in terms of a simple tight-binding approach for the -electrons of carbon, which yields a gapless linear band structure with a vanishing density of states at zero doping.^{2,3}

The electronic band structure of an undoped single graphene sheet allows for a description of the electronic properties in terms of an electrone eld theory which is equivalent to Quantum Electrodynamics (QED) in 2+1 dimensions. Within such a framework important physical quantities such as the electron self-energy or the charge and spin susceptibilities can be calculated exploiting the special symmetries of the model.

Finite doping away from half-lling qualitatively changes the above description, since it breaks electron-hole symmetry and also the pseudo Lorentz invariance needed for the equivalence with QED in two space dimensions. One is thus forced to retreat to conventional condensed-matter techniques such as e.g. Matsubara Green's functions. This was recently done for the static susceptibility of graphene at nite doping. Similar calculations for bulk graphite had been performed by Shung et al., who investigated the dielectric function and the plasm on behavior. Studies of static screening in graphene based on the Thomas-Ferm i approximation had also been considered. The relation between the polarization and the transport properties of graphene has been recently discussed in Refs. 5,9,10. Themo-plasma polaritons in graphene are discussed in citeVafek.

In this paper, we calculate the dynam ical polarization within the random phase approximation (RPA) for arbitrary wavevector, frequency, and doping. We discuss the method of calculation in the next section. We present in Section III results for static screening, where we analyze the Friedel oscillations induced by a charged or magnetic impurity, comparing our results with those of the two-dimensional electron gas (2DEG). Section IV discusses the plasm on dispersion relation and lifetime. In Section V we analyze the screening of the longitudinal acoustic modes by the conduction electrons. Finally, Section VI presents the main conclusions of our work. Some of the more technical aspects of the formalism are explained in the Appendix.

II. RPA CALCULATION

W ithin the e ective mass approximation, and focusing on one of the two unequal K - points, the Ham iltonian of an hexagonal graphene sheet is given in the Bloch spinor representation as

Here $_k = k_x + ik_y$ and $_k = (a_k; b_k)^T$, where a_k and b_k are the destruction operators of the B loch states of the two triangular sublattices. We have also introduced the Ferm i wavevector k_F which is related to the chemical potential via $k_F = -hy$. The Ferm i velocity $v_F = 3at=2\,h$ is determined by the carbon-carbon distance $a = 1.42\,A$ and the nearest neighbor hopping energy $t = 2.7\,eV$ resulting in v_F ' 9 10 m/s. We note that the elective Hamiltonian given above is valid only for wave vectors k , where ' 8.25 eV is a high-energy cuto stemming from the discreteness of the lattice. In the second of the lattice.

The quantity of interest form any physical properties is the dynam ical polarization, since it determ ines e.g. the electron-electron interaction, the Friedeloscillations and the plasm on and phonon spectra. In terms of the bosonic M atsubara frequencies $!_n = 2$ n = 1, it is defined as $!_n = 2$ n = 1.

$$P(q;i!_n) = \frac{1}{A} \int_{0}^{Z} d e^{i!_n} h T(q;) (q; 0)i;$$
 (2)

where A denotes the area. The average is taken over the canonical ensemble and the density operator is given by the sum of the density operators of the two sub-lattices = a + b. This amounts to working in the long-wavelength limit. To instorder in the electron-electron interaction, we obtain

$$P^{(1)}(q;i!_{n}) = \frac{g_{s}g_{v}}{4^{2}}^{Z} d^{2}k \int_{s:e^{0}=}^{x} f^{ss^{0}}(k;q) \frac{n_{F}(E^{s}(k))}{E^{s}(k)} \frac{n_{F}(E^{s^{0}}(k+q))}{E^{s^{0}}(k+q) + ih!_{n}};$$
 (3)

with E (k) = hyk the eigenenergies, r_F (E) = (e ^E + 1) ¹ the Ferm i function, and $g_S = g_V = 2$ the spin and valley degeneracy. A characteristic di erence between the polarization of graphene and that of a 2D EG is the appearance of the prefactors f^{ss^0} (k;q) coming from the band-overlap of the wave functions^{5,6}

$$f^{ss^0}(k;q) = \frac{1}{2} 1 + ss^0 \frac{k + q cos'}{k + qj}$$
; (4)

where ' denotes the angle between k and q.

At zero tem perature, the Ferm i functions yield sim ple step functions. We de ne the following retarded function by replacing $i!_n ! ! + i$

$$_{D} (q;!) = \frac{g^{Z}}{4^{2}h} d^{2}k \int_{k}^{X} \frac{f(k;q)}{! + v_{F}(k + q) + i};$$
 (5)

where $g=g_1g_V$. The + () sign corresponds to intra (inter)-band transitions and D is a general upper lim it.

For = 0, the retarded polarization thus reads

$$P_0^{(1)}(q;!) = (q;!)$$
: (6)

For > 0, i.e., for nonzero electron doping, the retarded polarization has an additional term

$$P^{(1)}(q;!) = {}^{+}(q;!) + {}^{+}(q;!)$$
: (7)

In the Appendix we give additional details of the calculation of Eq. (5). Here we sum – marize these expressions in terms of two complex functions, F (q;!) and G (x), defined as

$$F(q;!) = \frac{g}{16} \frac{h_{Y}^{2} q^{2}}{!^{2} v_{Y}^{2} q^{2}}; \quad G(x) = x^{p} \frac{1}{x^{2} 1} \ln x + p \frac{1}{x^{2} 1}$$
(8)

From now on it is always assumed that !>0, noting that the polarization for !<0 is obtained via $P^{(1)}(q; !) = P^{(1)}(q; !)$. Equations (6) and (7) are then rewritten in the following compact form

$$P^{(1)}(q;!) = P_0^{(1)}(q;!) + P^{(1)}(q;!);$$
 (9)

with

$$P_0^{(1)}(q;!) = i \frac{F(q;!)}{R^2 v_F^2};$$
 (10)

and

$$P^{(1)}(q;!) = \frac{g}{2 \text{ h}^{2} \text{v}_{F}^{2}} + \frac{F(q;!)}{\text{h}^{2} \text{v}_{F}^{2}} + \frac{F(q;!)}{\text{h}^{2} \text{v}_{F}^{2}} + \frac{h! + 2}{\text{h}^{2} \text{q}} = \frac{2 \text{ h}!}{\text{h}^{2} \text{q}} + 1 \text{ G} = \frac{h! + 2}{\text{h}^{2} \text{q}} = \frac{2 \text{ h}!}{\text{h}^{2} \text{q}} = \frac{2 \text{$$

Equations (9)-(11) are the main result of this work. Details of the calculation are given in the Appendix, where we also give expressions for the real and imaginary part of the polarization in terms of real functions.

Two lim its of the polarization are of particular in portance: (i) The long wavelength lim it $q! \ 0$ with $! > v_F q$ xed, which is relevant for optical spectroscopy and for the plasm a dispersion. (ii) The static case ! = 0 with q arbitrary, which is relevant for the screening of charged or magnetic in purities.

For the rst case we obtain

$$P^{(1)}(q! 0;!) = \frac{qq^2}{8 h!} \frac{h^2}{h!} + \frac{1}{2} \ln \frac{2 h!}{2 + h!} = \frac{1}{2} (h! 2);$$
 (12)

And for the second case we recover previous results⁵

$$P^{(1)}(q;0) = \frac{gk_F}{2 h_V} + (q 2k_F) \frac{gq}{8 h_V} G_{<} \frac{2k_F}{q} ; \qquad (13)$$

where $G_<(x)$ is the real function (for jxj<1) given in Eq. (A2). Note that for the absolute value of the polarization is linear in q, and acquires rapidly the behavior of $P_0^{(1)}$. By contrast, the polarization of the ordinary 2DEG decreases with increasing wave vector for $q>2k_F$. Furtherm ore, and also in contrast to the 2DEG, where the rst derivative of the static polarization is discontinuous at $q=2k_F$, doped graphene has a continuous rst derivative at $h_Fq=2$ and a discontinuous second derivative.

Table I sum marizes the ! dependence of Im P $^{(1)}$ for ! ! 0 for a 2D EG and for doped graphene. While the dependence is the same for $q \in 2k_F$, a subtle difference appears at $q = 2k_F$. This difference is intimately related to the nonanalytic behavior (as a function of q) of the static polarization at $q = 2k_F$. It leads to e.g. a different power law decay of the electron screening, as will be shown in subsection III. Table I also indicates that, depending on the order in which the limits q; ! 0 are taken, the low-frequency behavior may be that of an insulator, a metal, or a hybrid between the two.

The polarization is a continuous function of q and ! except for the square-root divergence which F (q;!) shows at ! = v_F q. Figure 1 shows real and imaginary parts of the polarization given by Eq. (9). We note that Im P ⁽¹⁾ (q;!) = 0 for hy q < h! < 2 hy q or 0 < h! < hy q 2, and negative otherwise, while ReP ⁽¹⁾ (q;!) < 0 for ! < v_F q.

The divergence at ! = v_F q vanishes in the self-consistent RPA result of the polarization given by 13

$$P_{RPA}(q;!) = \frac{P^{(1)}(q;!)}{1 - qP^{(1)}(q;!)} :$$
 (14)

Here $v_q = e^2 = 2_0 q$ denotes the in-plane Coulomb potential in vacuum. We note that $P_{RPA}(q;v_Fq) = v_q$ so that the self-consistent polarization has a real and nite value at

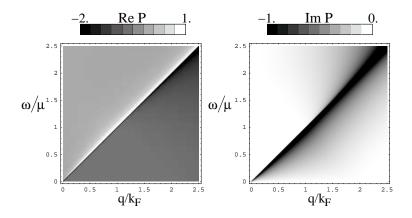


FIG. 1: Density plot of ReP $^{(1)}$ (q;!) (left) and Im P $^{(1)}$ (q;!) (right) in units of $=h^2v_F^2$. We set $h=v_F=1$.

	y < 1	y = 1	y > 1
2D E G	!	! 1=2	0
graphene	!	! ³⁼²	0

TABLE I: Low-frequency dependence of jm P $^{(1)}$ j in the lim it ! ! 0 for a 2D EG and for doped graphene. Here y $q=2k_F$.

 $!=v_F\,q$. Figure 2 shows real and imaginary parts of the self-consistent polarization. While the singularity at $!=v_F\,q$ is absent, a new singularity appears in ReP_{RPA} (q;!) at $!/p^p\,\bar{q}$, which rejects the existence of plasmons, as will be discussed in subsection IV.

III. STATIC SCREENING

An external charge density $n^{\text{ext}}(r) = Ze$ (r) is screened by free electrons due to the Coulomb interaction. This results in the induced charge density n(r)

$$n(r) = \frac{Ze}{4^{2}}^{Z} d^{2}q - \frac{1}{(q;0)} 1 e^{iq} r; \qquad (15)$$

Here (q;0) $\lim_{t \to 0} (q;t)$. Within the RPA approximation

$$(q;!) = {}_{0} \quad \forall_{P}^{(1)}(q;!) :$$
 (16)

The e ective dielectric constant $_0$ includes high energy screening processes. We take $_0$ ' $2.4.^5$

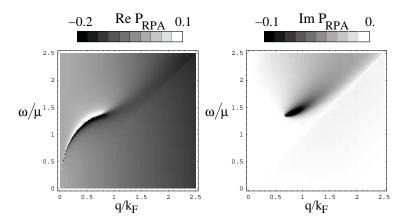


FIG. 2: Sam e as Fig. 1, for the renorm alized polarization P_{RPA} (q;!).

There are two contributions to the induced charge density. A non-oscillating part comes from the long-wavelength behavior of the polarization. This contribution is obtained within the Thomas-Ferm i (TF) approximation and is given by

$$n_{\rm TF}$$
 (r) ' $\frac{{\rm Ze}}{2~{\rm gk_F}~{\rm r}^3}$; (17)

where $\hat{e}=4$ $_0$ hy ' 25. We note here that in a 2D EG the TF contribution also decays as r 3 .

The second contribution to the long distance behavior is oscillatory and comes from the non-analyticity of the polarization at $h_{\Psi} q = 2$. However, and quite importantly, in graphene the non-analyticity results from a discontinuity occurring only in second derivative, the rst derivative being continuous. This leads to an oscillatory decay

$$n_{\rm osc}(r) / \frac{Z e \cos(2k_{\rm F} r)}{k_{\rm F} (_0 + 2_{})^2 r^3};$$
 (18)

which contrasts with the behavior of a 2D EG, where Friedel oscillations scale like $n(r) / \cos(2k_F r) r^2$. This dierence has been previously noted in Refs. 8,16, where however TF screening was not considered. We emphasize here that, because the TF contribution is of the same order of magnitude as the oscillatory part, it is essential to consider both of them. Furthermore we note that, while the TF contribution to screening given in Eq. (17) is independent of the dielectric constant $_0$, the amplitude of the oscillatory part given in Eq. (18) decreases with increasing $_0$. In fact, our numerical calculations show that for large distances the induced density does not change sign even in the hypothetical case of $_0$ = 0 where the ratio between oscillatory and TF contribution would be maximal. This

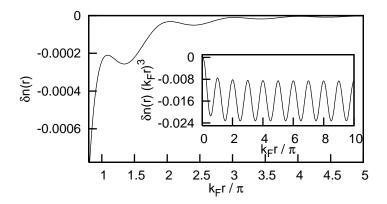


FIG. 3: Induced charge density n(r) (in units of k_F^2 Z e) as a function of the dimensionless variable k_F r=. The inset shows the r 3 decay at large distances. The high frequency screening is set to $_0$ = 2:4. In the used representation the graphs are invariant under a change of the chemical potential.

remarkable general property can be clearly appreciated in Fig. 3 for the particular case of $_0$ = 2:4: The induced density $_1$ n (r) does not change sign, but oscillates around a $_2$ nite o set.

The polarization also determ ines the Ruderm an-K ittel-K asuya-Yosida (RKKY) interaction energy between two magnetic impurities as well as the induced spin density due to a magnetic impurity, both quantities being proportional to the Fourier transform of $P^{(1)}(q;0)$. For a magnetic impurity at r the induced spin density m (r) is

m (r) / P (1) (r) =
$$\frac{1}{4^2}$$
 d^2qP (1) (q;0) e^{iq} r: (19)

Note that the magnetic response is proportional to the bare polarization, since the spin-spin interaction is mediated via the short ranged exchange interaction (in contrast to the long ranged C oulomb interaction in the case of charge response). That is why the TF contribution is missing and the induced spin density oscillates around zero. Figure 4 shows the numerically calculated $P^{(1)}(r)$ in units of $k_F^3 = h_F$ and illustrates this behavior. Specifically in the long wavelength $\lim_{r \to \infty} i r$ we obtain

m (r)
$$/\frac{\cos(2k_{\rm F} r)}{r^3}$$
; (20)

which is clearly seen in the inset of Fig 4. Like for the induced charge density, we not that the induced spin polarization m (r) decreases like r^3 for large distances. Again, this contrasts with the r^2 behavior found in a 2D EG. r^3 For the particular case of undoped

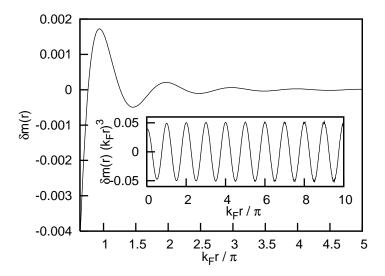


FIG. 4: Same as Fig. 3, for the induced spin density m(r).

graphene we recover the monotonous r^{3} decay obtained in Ref. 18.

Finally we note, that in contrast to the behavior of charge screening, where the induced charge scales like 1= at large distances, the envelop function of the spin density is independent of the chemical potential at large distances.

IV. PLASMONS

The plasm on dispersion is determined by solving for $(q; !_p i) = 0$, where is the decay rate of the plasm ons. For weak damping, the plasm on dispersion $!_p(q)$ and the decay rate are determined by $!_p(q)$

$$_{0} = v_{q}R eP^{(1)}(q;!_{p}); = \frac{Im P^{(1)}(q;!_{p})}{\frac{@}{@!}R eP^{(1)}(q;!) j_{p}} :$$
(21)

Solutions to the set equation only exist for $ReP^{(1)} > 0$, which is the case only for nite doping and $! > v_F q$. Furtherm ore, a stable solution requires $Im P^{(1)} = 0$, as is the case for region 1B of Fig. 6. Using the low-q expansion of the polarization given in Eq. (12), and neglecting the logarithm ic correction, we obtain

$$h!_{p}(q) = \frac{g \quad h \psi q}{2_{0}};$$
 (22)

with de ned below Eq. (17). The p \bar{q} behavior of the plasm on dispersion also appears in the 2D EG.

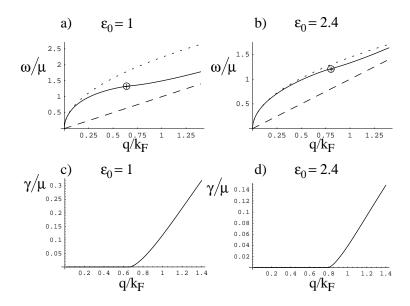


FIG. 5: Upper row: Solid lines show the dispersion relation for plasm onside ned by Re (q;!) = 0. Dotted lines show the low-q expansion of Eq. (22), while the dashed lines represents $! = v_F q$. The crosses indicate where the plasm ons acquire a nite lifetime. Lower row: Decay rate of plasm ons [see Eq. (21)] in units of them ical potential. We set h = 1.

O utside region 1B, the plasm on is damped, i.e. it has a nonzero decay rate. This can be clearly seen in Figs. 2 and 5. In the upper row of Fig. 5, we plot the exact plasm on dispersion for two dierent values of $_0$ and indicate the point at which the collective excitation becomes damped. The lower row shows the decay rate as obtained from Eq. (21).

Finally, it is interesting to note that the combination of the linear dispersion relation for quasiparticles [electrons above (or holes below) the Ferm ienergy] and the plasm on dispersion makes it impossible for a quasiparticle of energy h! to decay into a plasm on with q! = w. Hence, plasm ons with in nite lifetime do not contribute to the lifetime of quasiparticles.

V. ACOUSTIC PHONONS AND SOUND VELOCITY

We now calculate the dispersion and the decay rate of acoustical phonons in graphene. We treat the electrons in the -band of graphene as quasi-free electrons, while all the other electrons are assumed to be tightly bound to the carbon nuclei, thus forming electrons with a positive elementary charge. In the absence of screening by the conduction electrons, the ions oscillate at their plasma frequency due to the long range nature of the Coulomb

interaction. The collective modes of the combined electron—ion plasma can be obtained from the zeros of the total dielectric function $_{tot}(q;!)$, which is obtained by sum m ing the contributions from ions and electrons:

Here P_{el} ; $_{el}$ are the polarization and the dynam ical dielectric function of the electrons as given in Eqs. (9) and (16), while P_{ion} ; $_{ion}$ are the corresponding quantities for the ions. In the calculation of P_{ion} (q;!) we assume that the ions have a quadratic energy dispersion $E = h^2k^2 = 2M$ where M denotes the ion mass. The ionic charge density is two positive charges per unit cell, so that the Ferm i wave vector of the ions is k_F^0 (8 = A_c)¹⁼², where $A_c = 3 - 3a^2 = 2$ denotes the area of the hexagonal unit cell in real space. This value of k_F^0 is exact for elde ect doping and approximate for them ical doping.

In the calculation of P $_{ion}$ we assume that, for all relevant frequencies, we can take! hk_F^0 q=M . In the case of acoustic phonons this assumption is equivalent to v_s hk_F^0 =M ' $13 \ 10^4 v_F$, where v_s denotes the sound velocity. This relation is full led for all meaningful dopings as shown below. In this regime the ion polarization is real and given by

$$P_{ion}(q;!) = \frac{k_F^{0.2} q^2}{4 M!^2} = \frac{2E_0 q^2}{k^2 !^2};$$
 (24)

where we de ned $E_0 = h^2 = M A_c$ ' 7 10 5 eV . We note that E_0 is of the order of the ion con nem ent energy.

We may estimate the dispersion and the decay rate of the acoustical phonons by inserting Eq. (23) into Eq. (21). For nite doping > 0, the acoustic phonons at long wavelengths lie in the region 1A of Fig. 6 (de ned by ! < \sqrt{q} q < 2 = h !), where $R \in \mathbb{R}^{(1)}$ (q;!) = q = 2 $rac{1}{2}$ $rac{1}{2}$. In this regime the phonon dispersion is easily obtained:

$$!_{ph} = \frac{4 \quad E_0}{_0 \, h_{\Psi} \, q + g} \quad ^{1=2} v_F \, q$$
: (25)

To be consistent with the precondition $! < v_F q$ the expression in the square root has to be smaller than one. This sets a lower lim it to the values of the chem ical potential for which Eq. (25) is valid. The sound velocity v_s and the decay rate m ay be derived from Eqs. (21) and (25) in the lim it of low q. We obtain

$$v_s = {p - v_F ; = \frac{v_F q}{2^p 1};}$$
 (26)

with = $4 E_0 = g$.

Some additional remarks on the validity of Eq. (25) go in place. We have already said that, for q! 0, it only applies provided < 1. We also wish to note that the acoustical phonons are only well-de ned if their frequency is much larger than their decay rate, i.e. if $!_{ph} = 1$. Since $!_{ph} = 1$ for $!_{ph} = 4 = 1$, we conclude that the notion of acoustic phonons is justiled for $!_{ph} = 1$, which corresponds to $!_{ph} = 1$ for $!_{ph}$

We have assumed initially that $v_s = h k_F^0 = M$ ' 13 $10^4 v_F$. A coording to Eq. (26) this results in 1:7 10^8 , or equivalently, $10^8 E_0$, which is always full led.

We nish this section by estimating the sound velocity of a typical graphene sample. A ssum ing a concentration of "conduction-band" electrons of $n_{\rm el}=10^{10}-10^2~{\rm cm}^{-2}$ we get ' $10^{-2}-10^{-1}~{\rm eV}$. We note that this corresponds to ' $2-20-10^3$, so that Eqs. (25) and (26) are applicable, resulting in $v_{\rm s}$ ' $0.05-0.14\,{\rm g}$ " 4 12 10° m/s and ' $10^{-3}-10^{\circ}$ $v_{\rm F}$ q. These results suggest a signicant enhancement of the sound velocity, as compared to normal metals, where $v_{\rm s}$ " $v_{\rm F}=10^{-2}$ $v_{\rm F}=10^{-2}$ The low polarizability of the conduction electrons leads to a poor screening of the oscillations of the charged ions. On the other hand, in a semiconductor with a gap larger than the typical acoustic phonon frequencies, the electrons follow adiabatically the ions. In that case, the lattice vibrations can be described as oscillations of neutral particles.

VI. CONCLUSIONS

In this article we have derived a compact and closed expression for the dynam ical polarization of graphene within the RPA approximation. The obtained result is valid for arbitrary wave vector, frequency, and doping. As particular cases, we have derived the long-wavelength limit q! 0 and the static limit!! 0. We have employed the RPA polarization to calculate several physical quantities of interest in doped graphene. First we have studied the static Friedel oscillations of the induced charge (spin) density in the presence of a charged (magnetic) impurity. We have found that, although the charge density does show oscillations around an average value, it does it without changing sign. The reason for this remarkable behavior is that Friedel oscillations superpose on the dominant Thomas Ferm i induced density, with both contributions decaying at long distances r with the same power

 $law r^3$.

The dynam ical polarization has been used to calculate the dispersion relation and the decay rate of plasm on s and acoustic phonons. Like in the 2D EG case, the plasm on frequency shows a p \overline{q} -behavior in the long wavelength regime. We have determined the region in the (q;!) plane where the plasm on is stable, as well as the decay rate in the regime where it is not.

The dispersion of acoustical phonons has been shown to be strongly dependent on the chem ical potential. In particular, we have found that the sound velocity approaches the Ferm i velocity at low doping. However, the same limit shows an increase in the decay rate of acoustic phonons due to electron-hole pair excitation.

Although we have focused on applications of the RPA calculation to the case of doped graphene, some aspects of the low-frequency, long-wavelength dynamics of pure graphene appear to be intriguing and worth studying further.

Note added. When this work was about to be submitted, we became aware of a related paper. Overlapping results in the two papers are in agreement.

A cknow ledgem ents

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APPENDIX A: CALCULATION OF THE POLARIZATION

In the following we present some major steps of the calculation of the polarization. We restrict the discussion to ! > 0 since $P^{(1)}(q; !) = P^{(1)}(q; !)$. In all the Appendix we set $v_F = h = 1$, so that in the Appendix $= k_F$.

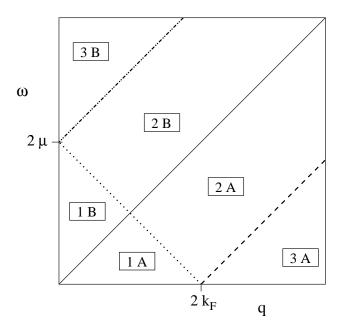


FIG. 6: D isplay of the dierent regions characterizing the susceptibility behavior. Regions are limited by straight lines! = $v_F q$ (solid), ! = $v_F q$ 2 (dashed) and ! = 2 $v_F q$ (dotted), where we set h = 1.

1. Im aginary part

The imaginary part of the functions $_{\rm D}$ (q;!) de ned in Eq. (5) has the following form

The '-integration yields

$$I = \frac{(2 + !)^2 + q^2}{q^2 !^2} \qquad () (q !) k \frac{q !}{2}$$

$$+ () (! q) () \frac{! + q}{2} k \frac{! q}{2} k ;$$

which is always real. The nalk-integration can now simply be performed. We obtain for = 0

In order to present the result for > 0, we introduce the real functions $f(q;!);G_>(x);G_<(x)$

$$f(q;!) = \frac{g}{16} \frac{q^{2}}{j!^{2}};$$

$$G_{>}(x) = x^{p} \frac{q^{2}}{x^{2}} + cosh^{1}(x); \quad x > 1;$$

$$G_{<}(x) = x^{p} \frac{q^{2}}{1 + x^{2}} + cosh^{1}(x); \quad \dot{x} \neq 1;$$
(A 2)

For the additional term at nite doping given by Eq. (7), we obtain in the language of Fig. 6

2. Realpart

The K ram ers-K ronig relation valid for the retarded function $ReP_0^{(1)}$ (q;!) reads

$$R \in \mathbb{P}_{0}^{(1)}(q;!) = \frac{1}{1} d! \frac{\lim_{s \to 0} \mathbb{P}_{0}^{(1)}(q;!)}{! \cdot i!} = \frac{gq^{2}}{16 q^{2} !^{2}} (q !)$$
(A 3)

For nite doping we rewrite Eq. (7) as

Re P (1)
$$(q;!) = \frac{g}{4^2} \int_{0}^{Z} dk k \int_{0}^{Z} d' \frac{X}{(k+!)^2 k+q^2}$$
:

This integral is calculated directly such that the K ram ers-K ronig relation is not needed, here. The '-integration yields

Re P (1) =
$$\frac{g}{2} + \frac{g}{8^2} \times \frac{Z}{a}$$
 dkJ^a (k;q;!); (A4)

where J (k;q;!) is given by

$$J = 2 \frac{(2 + !)^2 + q^2}{!^2 + q^2} \qquad (q !) \frac{q !}{2} \qquad k)$$

$$+ (! q) () + () \frac{! q}{2} k) \qquad (k \frac{! + q}{2}) \qquad :$$

We thus get in the language of Fig. 6

3. A nalytic representation

Concerning the analytic representation of the results given in Eq. (9), we note the following properties (see e.g. Ref 20)

(x 1)
$$\cosh^{1}(x) = \ln(x + \frac{p}{x^{2}} \frac{1}{1});$$

(1 x^{2}) $\cos^{1}(x) = i\ln(x + i\frac{p}{1} \frac{1}{x^{2}});$
 $\cos^{1}(x) = \cos^{1}(x):$

Thus the functions $G_{>}(x)$; $G_{<}(x)$ can be comprised by the single function G(x) $\ln (x + \frac{p}{x^2} - 1)$ where

$$G(x) = \begin{cases} 8 & & & \\ < G_{>}(x) & & ; x > 1 \\ \vdots & iG_{<}(x) = & i[+ G_{<}(x)]; jxj < 1 \end{cases}$$
 (A5)

We also note the relation f(q;!) = F(q;!)j, where f(q;!) is the real function dened in Eq. (A2) while F (q;!) is the complex function introduced in Eq. (8).

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